

HMC694LP4 / 694LP4E

v02.1108



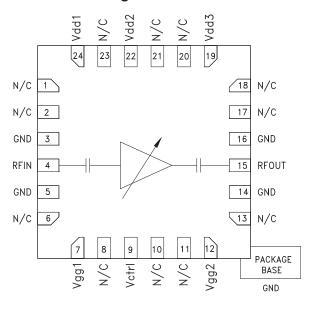
GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

Typical Applications

The HMC694LP4(E) is ideal for:

- · Point-to-Point Radio
- Point-to-Multi-Point Radio
- EW & ECM
- X-Band Radar
- Test Equipment

Functional Diagram



Features

Wide Gain Control Range: 23 dB

Single Control Voltage

Output IP3 @ Max Gain: +30 dBm

Output P1dB: +22 dBm No External Matching

24 Lead 4x4 mm SMT Package: 16 mm²

General Description

The HMC694LP4(E) is a GaAs MMIC PHEMT analog variable gain amplifier which operates between 6 and 17 GHz. Ideal for microwave radio applications, the amplifier provides up to 22 dB of gain, output P1 dB of up to +22 dBm, and up to +30 dBm of output IP3 at maximum gain, while requiring only 175 mA from a +5V supply. A gate bias pin (Vctrl) is provided to allow variable gain control up to 23 dB. Gain flatness is excellent making the HMC694LP4E ideal for EW, ECM and radar applications. The HMC694LP4E is housed in a RoHS compliant 4x4 mm QFN leadless package and is compatible with high volume surface mount manufacturing.

Electrical Specifications, $T_A = +25$ °C, Vdd1, 2, 3= 5V, Vctrl= -2V, Idd= 170 mA*

| Parameter | Min. | Тур. | Max. | Min. | Тур. | Max. | Units |
|--|------|--------|------|------|---------|------|--------|
| Frequency Range | | 6 - 10 | | | 10 - 17 | | GHz |
| Gain | 19 | 22 | | 14 | 18 | | dB |
| Gain Flatness | | ±1 | | | ±1.5 | | dB |
| Gain Variation Over Temperature | | 0.015 | | | 0.015 | | dB/ °C |
| Gain Control Range | | 23 | | | 20 | | dB |
| Noise Figure | | 6 | 7.5 | | 6 | 6.5 | dB |
| Input Return Loss | | 15 | | | 8 | | dB |
| Output Return Loss | | 10 | | | 8 | | dB |
| Output Power for 1 dB Compression (P1dB) | 19 | 21 | | 21 | 22 | | dBm |
| Saturated Output Power (Psat) | | 22 | | | 23 | | dBm |
| Output Third Order Intercept (IP3) | | 30 | | | 30 | | dBm |
| Total Supply Current (Idd) | | 175 | | | 175 | | mA |

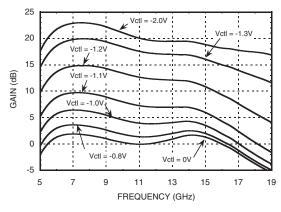
^{*}Set Vctrl = -2V and then adjust Vgg1, 2 between -2V to 0V (typ. -0.8V) to achieve Idd = 170mA typical.



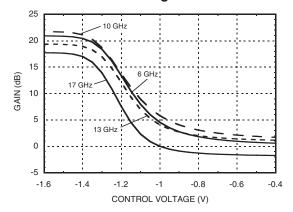


GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

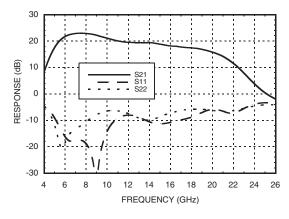
Control Voltage Range vs. Gain



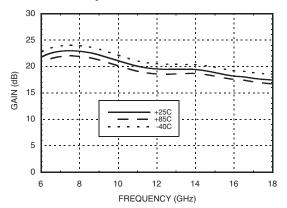
Gain vs. Control Voltage



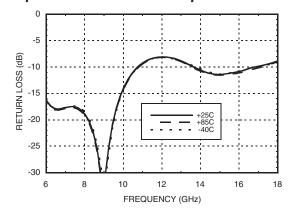
Broadband Gain & Return Loss



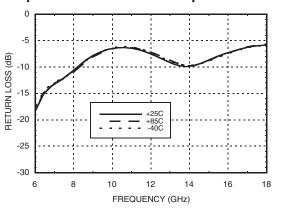
Gain vs. Temperature



Input Return Loss vs. Temperature



Output Return Loss vs. Temperature

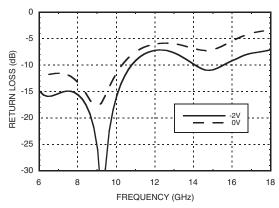




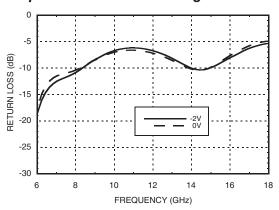


GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

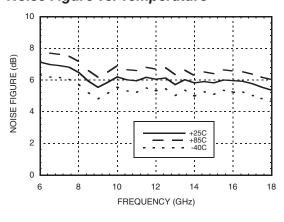
Return Loss @ Voltage Extreme



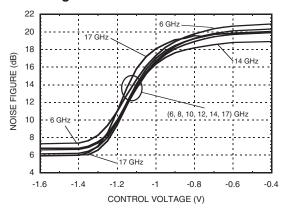
Output Return Loss @ Voltage Extreme



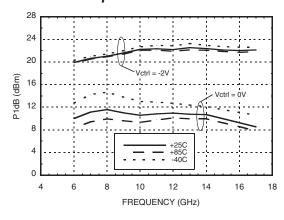
Noise Figure vs. Temperature



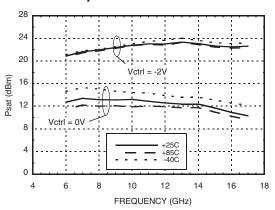
Noise Figure vs. CTRL



P1dB vs. Temperature



Psat vs. Temperature



[1] Tested with broadband bias tee on RF ports and C1 = 10,000pF

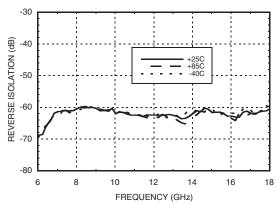
[2] C1, C6 and C8 = 100pF, L1 = 24nF



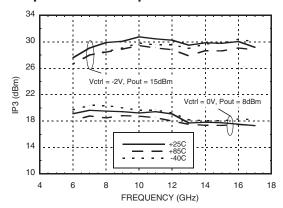


GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

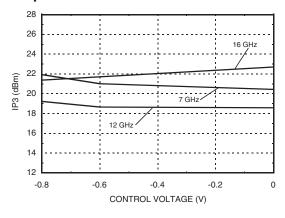
Reverse Isolation vs. Temperature



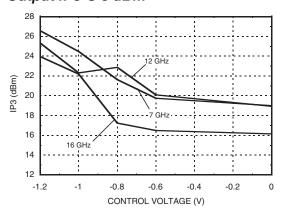
Output IP3 vs. Temperature



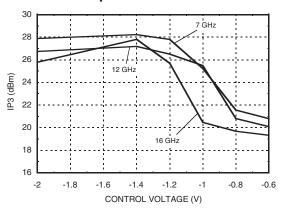
Output IP3 @ 0 dBm



Output IP3 @ 5 dBm



Output IP3 @ 10 dBm







GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

Absolute Maximum Ratings

| Drain Bias Voltage (Vdd1, 2, 3) | +5.5V | |
|---|----------------|--|
| Gate Bias Voltage (Vgg1, 2) | -3 to 0V | |
| Gain Control Voltage (Vctrl) | -3 to 0V | |
| RF Power Input | +5 dBm | |
| Channel Temperature | 175 °C | |
| Continuous Pdiss (T = 85 °C) (derate 10.2 mW/°C above 85 °C) [1] | 0.92 W | |
| Thermal Resistance (Channel to ground paddle) | 97.6 °C/W | |
| Storage Temperature | -65 to +150 °C | |
| Operating Temperature | -40 to +85 °C | |

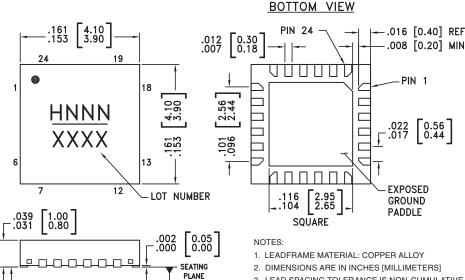
Bias Voltage

| Vdd1,2,3 (V) | Idd Total (mA) | | |
|--------------|----------------|--|--|
| +5.0 | 170 | | |
| Vgg1,2 (V) | Igg Total (mA) | | |
| 0V to -2V | <3 μΑ | | |



ELECTROSTATIC SENSITIVE DEVICE **OBSERVE HANDLING PRECAUTIONS**

Outline Drawing



- 3. LEAD SPACING TOLERANCE IS NON-CUMULATIVE.
- 4. PAD BURR LENGTH SHALL BE 0.15mm MAXIMUM. PAD BURR HEIGHT SHALL BE 0.05mm MAXIMUM.
- 5. PACKAGE WARP SHALL NOT EXCEED 0.05mm.
- 6. ALL GROUND LEADS AND GROUND PADDLE MUST BE SOLDERED TO PCB RF GROUND.
- 7. REFER TO HITTITE APPLICATION NOTE FOR SUGGESTED LAND PATTERN.

Package Information

☐ .003[0.08] C

| Part Number | Package Body Material | Lead Finish | MSL Rating | Package Marking [3] |
|-------------|--|---------------|------------|---------------------|
| HMC694LP4 | Low Stress Injection Molded Plastic | Sn/Pb Solder | MSL1 [1] | H694 XXXX |
| HMC694LP4E | RoHS-compliant Low Stress Injection Molded Plastic | 100% matte Sn | MSL1 [2] | H694 XXXX |

-C-

- [1] Max peak reflow temperature of 235 °C
- [2] Max peak reflow temperature of 260 $^{\circ}\text{C}$
- [3] 4-Digit lot number XXXX





GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

Pin Descriptions

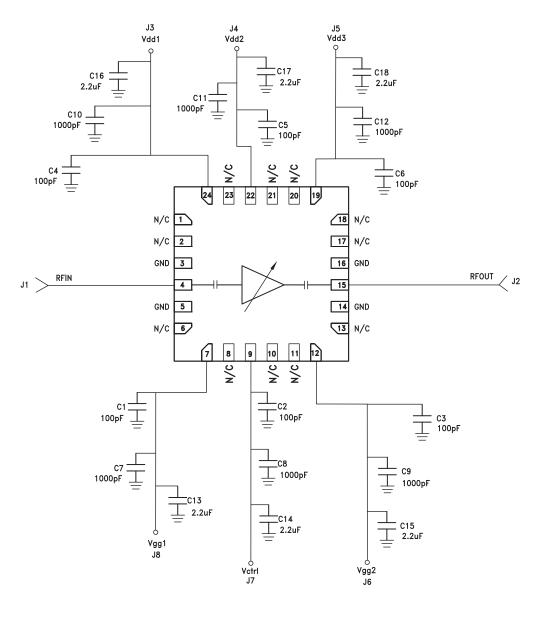
| Pad Number | Function | Description | Interface Schematic |
|--|------------|---|---------------------|
| 1, 2, 6, 8, 10, 11, 13, 17, 18, 20, 21, 23 | N/C | No Connection | |
| 3, 5, 14, 16 | GND | Die bottom must be connected to RF/DC ground. | GND = |
| 4 | RFIN | This pad is AC coupled and matched to 50 Ohm. | RFIN O—— |
| 7, 12 | Vgg1, 2 | Gate control for amplifier. Adjust voltage to achieve typical Idd. Please follow "MMIC Amplifier Biasing Procedure" application note. | Vgg1,2 |
| 9 | Vctrl | Gain control Voltage for the amplifier. See assembly diagram for required external components. | Vetrl O |
| 15 | RFOUT | This pad is AC coupled and matched to 50 Ohm. | — —○ RFOUT |
| 19, 22, 24 | Vdd1, 2, 3 | Drain Bias Voltage for the amplifier. See assembly diagram for required external components | OVdd1,2,3 |





GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

Application Circuit



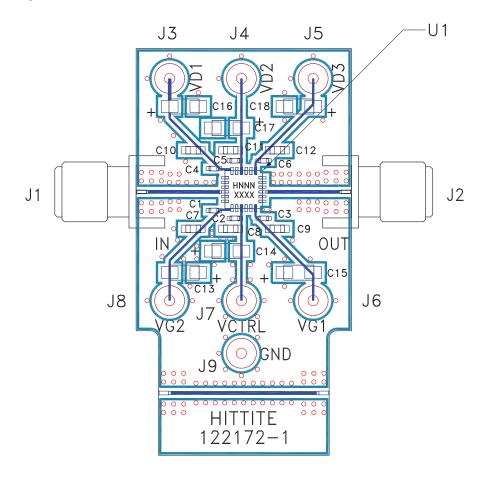


HS✓

v02.1108

GaAs MMIC ANALOG VARIABLE GAIN AMPLIFIER, 6 - 17 GHz

Evaluation PCB



List of Materials for Evaluation PCB 122174 [1]

| Item | Description |
|-----------|--------------------------------------|
| J1, J2 | PCB Mount SMA RF Connectors |
| J3 - J9 | DC Pin |
| C1 - C6 | 100 pF Capacitor, 0402 Pkg. |
| C7 - C12 | 1000 pF Capacitor, 0603 Pkg. |
| C13 - C18 | 2.2 µF Capacitor, CASE A |
| U1 | HMC694LP4(E) Variable Gain Amplifier |
| PCB [2] | 122172 Evaluation PCB |

^[1] Reference this number when ordering complete evaluation PCB

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation circuit board shown is available from Hittite upon request.

^[2] Circuit Board Material: Arlon 25FR

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Amplifier category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

A82-1 BGA622H6820XTSA1 BGA 728L7 E6327 BGB719N7ESDE6327XTMA1 HMC397-SX HMC405 HMC561-SX HMC8120-SX HMC8121-SX HMC-ALH382-SX HMC-ALH476-SX SE2433T-R SMA3101-TL-E SMA39 A66-1 A66-3 A67-1 A81-2 LX5535LQ LX5540LL MAAM02350 HMC3653LP3BETR HMC549MS8GETR HMC576-SX HMC-ALH435-SX SMA101 SMA32 SMA411 SMA531 SST12LP19E-QX6E WPM0510A HMC5879LS7TR HMC1087F10 HMC1086 HMC1016 SMA1212 MAX2689EWS+T MAAMSS0041TR MAAM37000-A1G LTC6430AIUF-15#PBF SMA70-2 SMA4011 A231 HMC-AUH232 LX5511LQ LX5511LQ-TR HMC7441-SX HMC-ALH310 XD1001-BD-000V A4011